

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1542** is a Common Base Device Designed for, IFF and DME Pulse Applications.

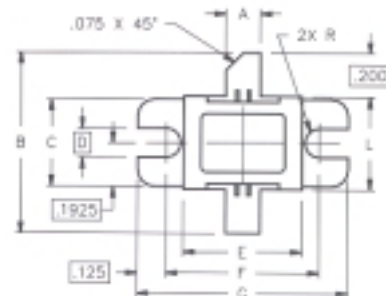
FEATURES INCLUDE:

- Gold Metalization
- Input/Output Matching
- Hermetically Sealed

MAXIMUM RATINGS

I_C	40 A
V_{CES}	65 V
V_{CBO}	65 V
P_{DISS}	1350 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$
θ_{JC}	0.06 $^\circ C/W$

PACKAGE STYLE .400 X 500 2L FLG



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.145/3.68	.155/3.93	I	.060/1.40	.065/1.65
B	.750/19.05		J	.115/2.92	.130/3.43
C	.380/9.65	.390/9.91	K		.230/5.84
D		.130/3.30	L	.395/10.03	.410/10.41
E	.495/12.57	.505/12.83			
F	.640/16.26	.655/16.64			
G	.880/22.61	.910/23.11			
H	.002/0.05	.006/0.15			

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 25$ mA	65			V
BV_{CES}	$I_C = 50$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	3.5			V
I_{CES}	$V_{CE} = 50$ V			35	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 250$ mA	5.0		200	---
P_G P_{OUT}	$V_{CC} = 50$ V $P_{IN} = 150$ W $f = 1025$ to 1150 MHz PULSE WIDTH = $10 \mu S$ DUTY CYCLE = 1.0%	5.6 550			dB W